

General Description

These is N-channel MOSFET device that features a low on-state resistance and excellent switching characteristics, and designed for low voltage high current applications such as DC/DC converter with synchronous rectifier.

Features

- Simple Drive Requirement
- Low Gate Charge
- Fast Switching
- Ultra-Low RDS(on)
- Green Device Available

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current ¹	50	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current ¹	40	A
I_{DM}	Pulsed Drain Current ²	150	A
EAS	Single Pulse Avalanche Energy ³	55	mJ
I_{AS}	Avalanche Current	40	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	50	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	45	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction -Case ¹	---	2.5	$^\circ\text{C/W}$

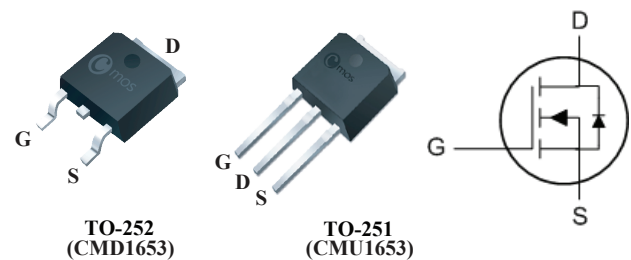
Product Summary

BVDSS	RDSON	ID
30V	8m Ω	50A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- DC/DC converter
- Motor drives

TO-252/251 Pin Configuration



N-Ch 30V Fast Switching MOSFETs
Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=250\mu A$	---	0.023	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=30A$	---	6.5	8	$m\Omega$
		$V_{GS}=4.5V, I_D=20A$	---	11	14	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1	---	3	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5	---	mV/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=24V, V_{GS}=0V, T_J=150^\circ\text{C}$	---	---	10	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=10A$	---	35	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	2.4	---	Ω
Q_g	Total Gate Charge	$V_{DS}=15V, V_{GS}=4.5V, I_D=20A$	---	12	---	nC
Q_{gs}	Gate-Source Charge		---	4.5	---	
Q_{gd}	Gate-Drain Charge		---	6	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V, V_{GS}=10V, R_G=3.3\Omega, I_D=20A$	---	10	---	ns
T_r	Rise Time		---	25	---	
$T_{d(off)}$	Turn-Off Delay Time		---	20	---	
T_f	Fall Time		---	14	---	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	950	---	pF
C_{oss}	Output Capacitance		---	380	---	
C_{rss}	Reverse Transfer Capacitance		---	180	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ¹	$V_G=V_D=0V$, Force Current	---	---	50	A
I_{SM}	Pulsed Source Current ²		---	---	150	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=20A, T_J=25^\circ\text{C}$	---	---	1.2	V

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.

2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

3.The EAS data shows Max. rating . The test condition is $V_{DD}=15V, V_{GS}=10V, L=1.0mH, I_{AS}=10A$

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